ABSTRACT

The present technology includes a memory device and a method of operating the same. The memory device includes a string including a first select transistor, memory cells, and a second select transistor connected between a source line and a bit line, and a voltage generator supplying a precharge voltage to the source line and selectively applying a turn on voltage or a negative voltage to a first select line connected to a gate of the first select transistor. The voltage generator applies the precharge voltage to the source line, applies the turn on voltage to the first select line during a first time in which a channel layer of the string is precharged, and applies the negative voltage to the first select line during a second time in which the channel layer of the string is precharged, while precharging the channel layer of the string.

FIG. 5